



SUP85N15-21-E3 Information



For Reference Only

Part Number SUP85N15-21-E3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 150V 85A TO220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SUP85N15-21-E3 Specifications

Manufacturer Part Number SUP85N15-21-E3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 150V Current - Continuous Drain (Id) @ 25°C 85A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4750pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.4W (Ta), 300W (Tc) Rds On (Max) @ Id, Vgs 21 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C85A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4750pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.4W (Ta), 300W (Tc)Rds On (Max) @ Id, Vgs21 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C85A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4750pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.4W (Ta), 300W (Tc)Rds On (Max) @ Id, Vgs21 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	TrenchFET?
Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C85A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4750pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.4W (Ta), 300W (Tc)Rds On (Max) @ Id, Vgs21 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 85A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4750pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.4W (Ta), 300W (Tc) Rds On (Max) @ Id, Vgs 21 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4750pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.4W (Ta), 300W (Tc)Rds On (Max) @ Id, Vgs21 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	150V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	85A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 4750pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 21 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 21 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.4W (Ta), 300W (Tc)Rds On (Max) @ Id, Vgs21 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	110nC @ 10V
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	4750pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 21 mOhm @ 30A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs21 mOhm @ 30A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	2.4W (Ta), 300W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	21 mOhm @ 30A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

SUP85N15-21-E3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SUP85N15-21-E3 Payment Methods



















SUP85N15-21-E3 Shipping Methods













If you have any question about SUP85N15-21-E3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com